

Design & Reuse, IP SoC Day
Shanghai 2nd September 2016
Shortform Presentation

The Challenges Posed by In-Chip Conditions to Reaching Working Silicon

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20 mins
11.25am

GLOBAL IN-CHIP MONITORING

Advanced Node Design

Scaling from 28nm to 7nm

Gate Density

Power Density

Thermal Density

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Gate Density

Power Density
Complexity

Thermal Density
IR Drop & Noise

GLOBAL IN-CHIP MONITORING

Advanced Node Design

Scaling from 28nm to 7nm

Gate Density

Power Density
Complexity
Process Variance

Thermal Density
IR Drop & Noise
Timing Closure

Reliability
Performance

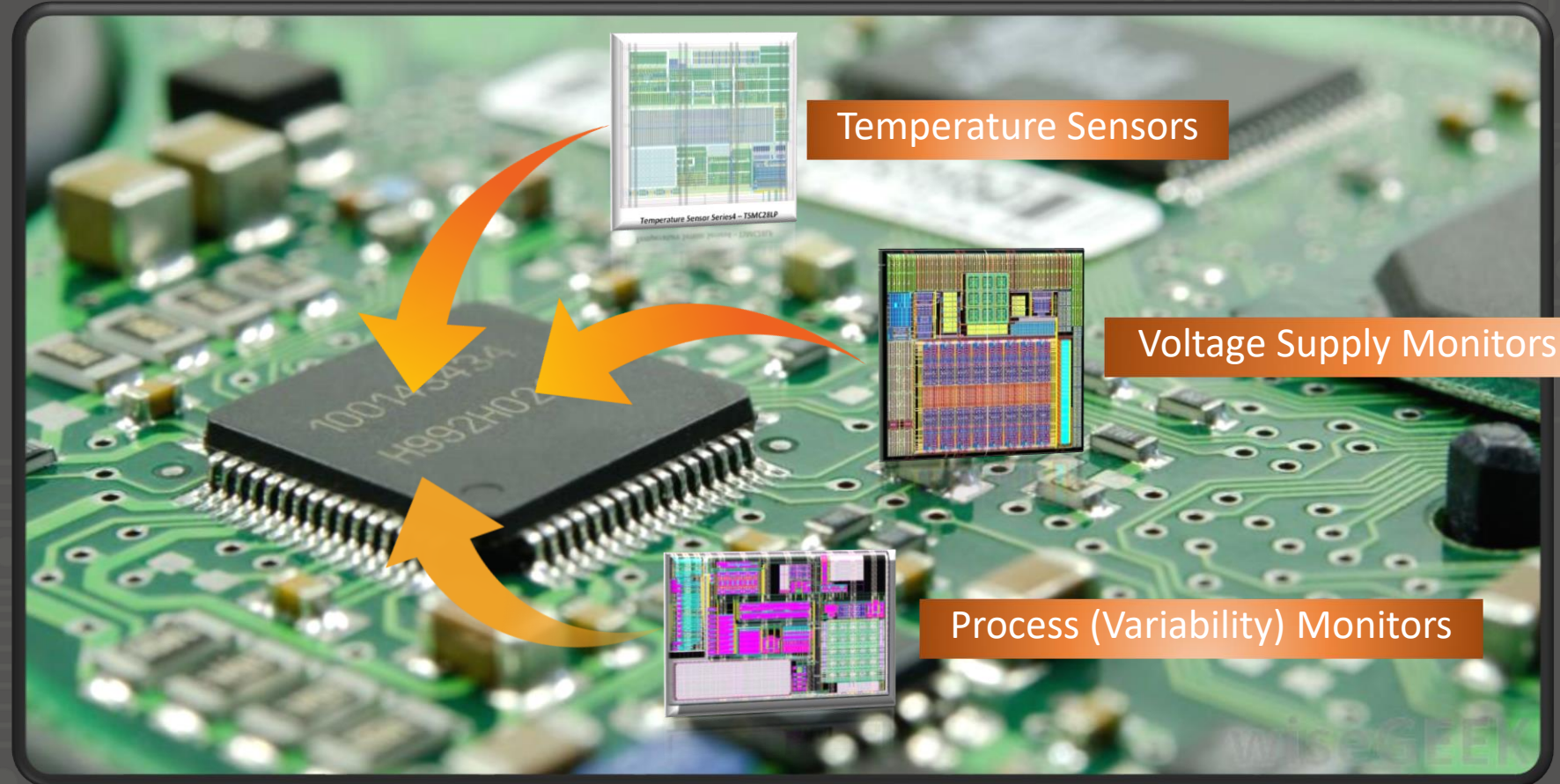
GLOBAL IN-CHIP MONITORING

In-Chip Monitoring

Measure

Monitor

Optimise



GLOBAL IN-CHIP MONITORING

Challenges

- In-Chip Conditions
 - Process – Static condition
 - Voltage & Temperature - Dynamic
- Design Challenges
 - Working silicon & Performing Silicon
 - Optimisation & Design Trade offs
 - Monitoring – speed & accuracy
 - Trust in your IP
- What is the ideal solution?



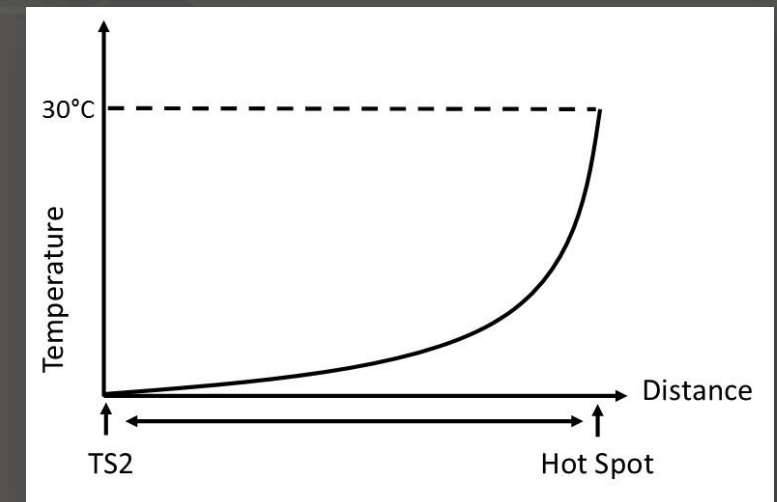
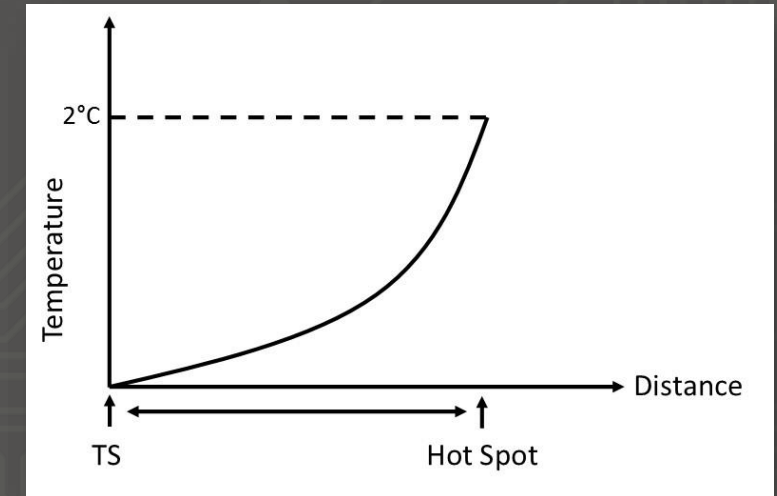
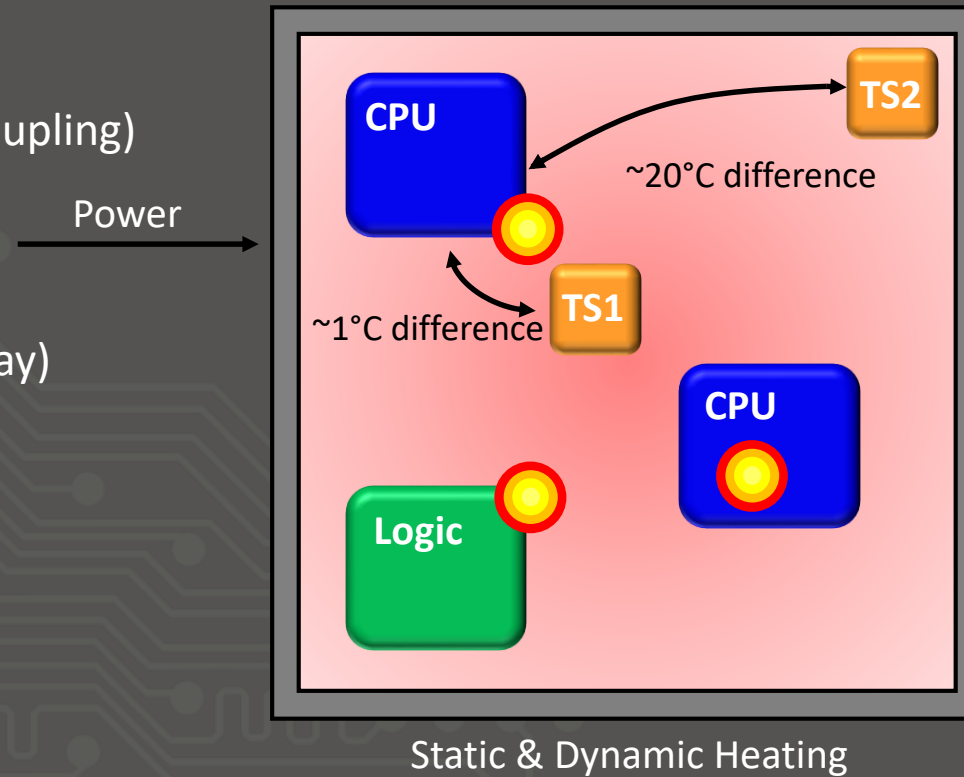
Thermal Challenges

What is happening on chip?

- Hot spots
- Thin tracks (thermal coupling)
- Electro Migration
- Power (thermal runaway)

Design challenge

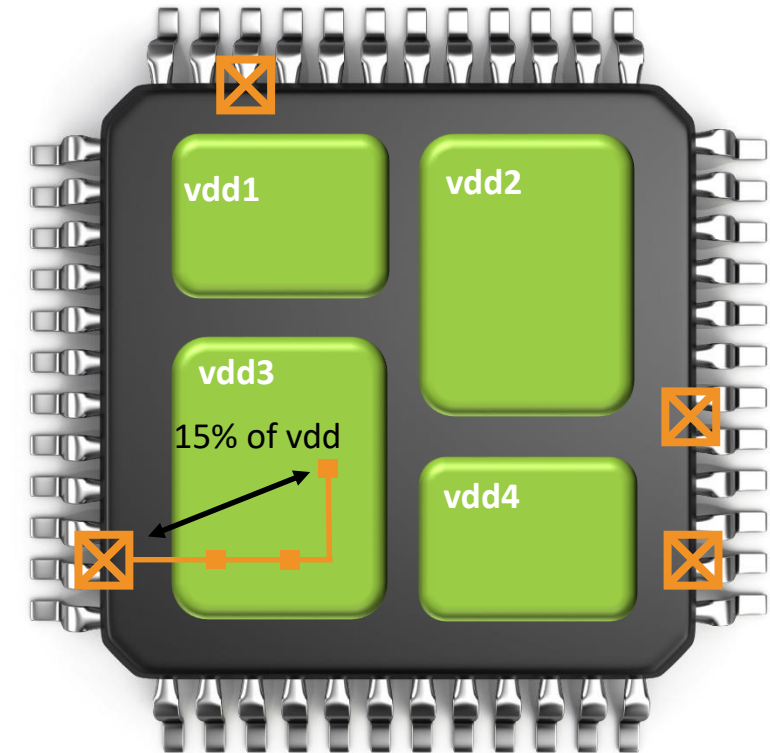
- Where to monitor?
- How to use monitor information?



Supply Challenges

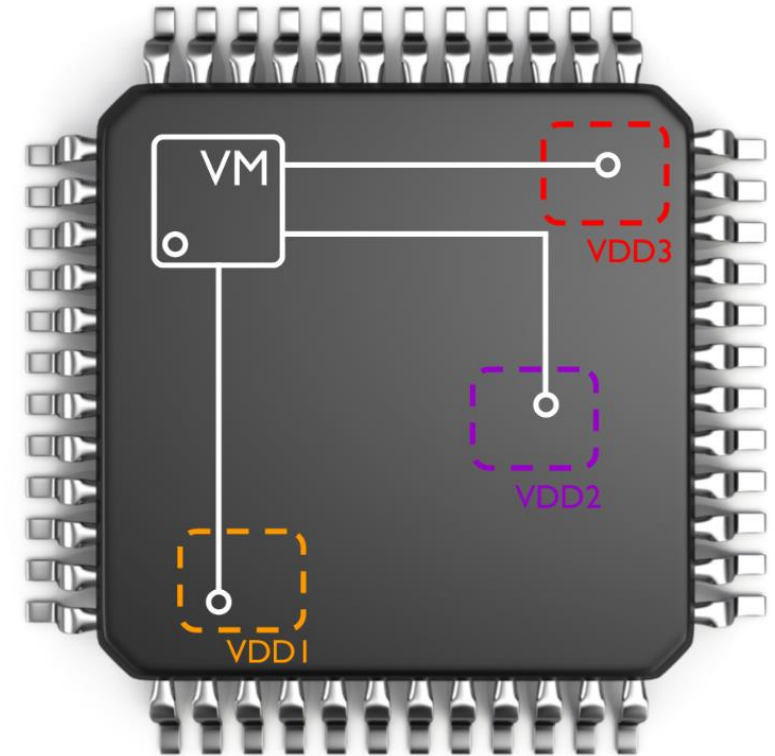
What is happening on-chip?

- IR Drops
- Vt is relatively static yet headroom as reduced.
 - Eg. Finfet with extremely low vdd
- Interconnect & via resistances increasing
- Lose state, crossing Vt esp if transient events.
- Vdd conditions may violate timing



Supply Challenges

- Dynamic power
 - Planar is leakage dominated
 - FinFET is activity dominated (bouncy supplies!)
- Therefore accurate measurement, tight control, quick regulator response.
- Maintain headroom if possible

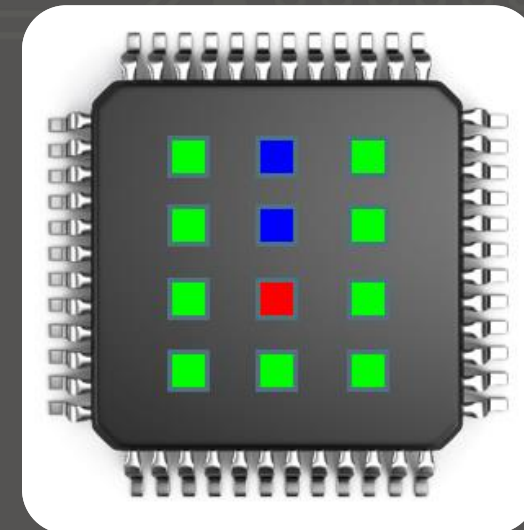
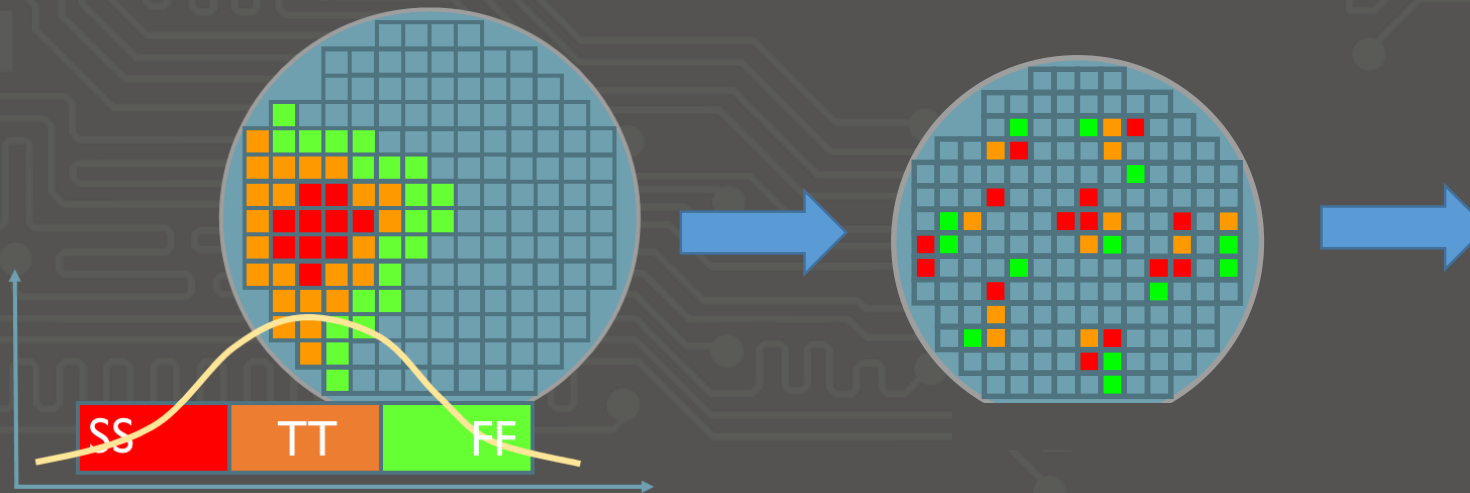


Process Challenges

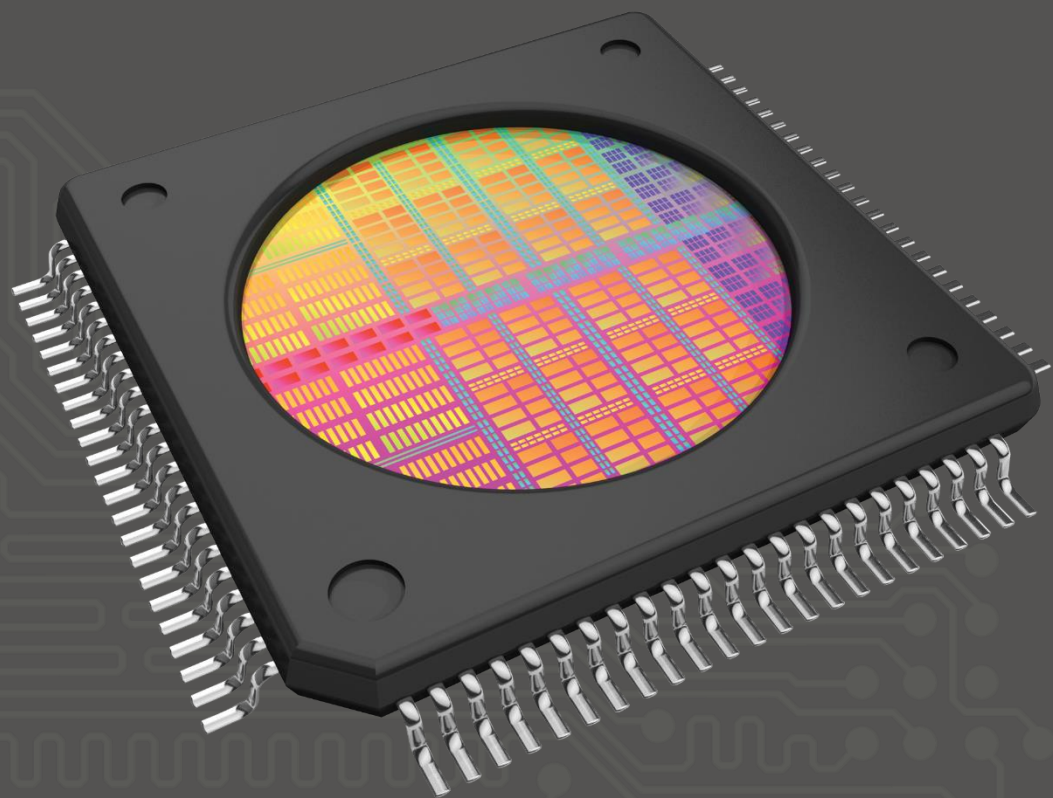
What's happening on chip?

- Increased Process Variability:
 - Multi patterning
 - Metal resistance variability increasing
 - Via resistance
 - Interconnect track lengths increasing

- Sensitivities to VT variation
- Aging: Gm degradation and Vt shift with aging
- Bias Temperature Instability, BTI (Vt increasing)
- Hence, greater gate delay variability

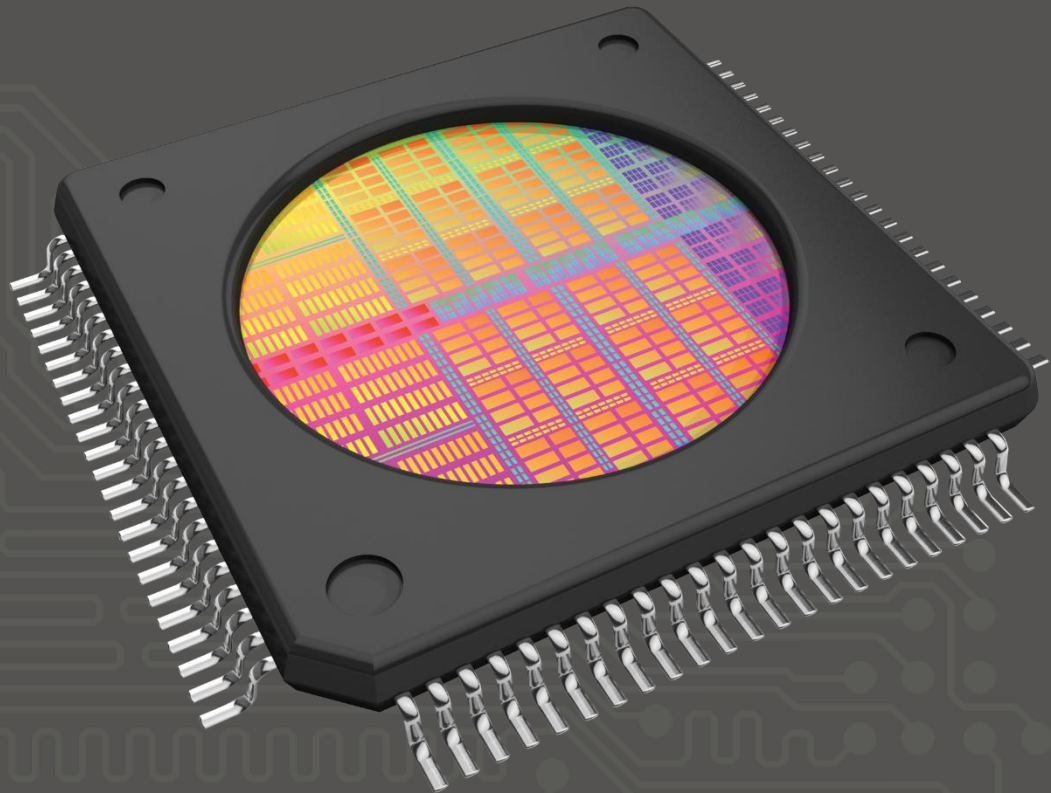


Summary



- Key Challenges:
 - Timing Closure Issue
 - Reliability
 - Thermal dissipation vs Moore's Law
- New Design Methodologies
 - Design for *Thermal* (DFT)
 - Holistic Thermal analysis of Package & Die
 - Data!
- Opportunities
 - Optimisation
 - Accurate, trusted monitoring

Thank you



Global In-Chip Monitoring

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